

Rev. 1.4

1024K X 16 BIT HIGH SPEED CMOS SRAM

REVISION HISTORY

<u>Revision</u>	<u>Description</u>	Issue Date
Rev. 1.0 Rev. 1.1	Initial Issued Add 48 pin BGA package type.	Jan.09. 2012 Mar.12. 2012
Rev. 1.2	1."CE# ≧Vcc - 0.2V" revised as "CE# ≦0.2" for TEST CONDITION of Average Operating Power supply Current Icc1 on page3 2.Revised ORDERING INFORMATION Page11	July.19. 2012
Rev. 1.3	1.Revise "TEST CONDITION" for VOH, VOL on page 3 IOH = -8mA revised as -4mA IOL =4mA revised as 8mA 2. Revise VIH(max) & VIL(min) note on page 3 VIH(max) = VCC + 2.0V for pulse width less than 6ns. VIL(min) = VSS - 2.0V for pulse width less than 6ns.	June. 04. 2013
Rev.1.4	Revised the address pin sequence of pin configuration of 48 pin TSOP-I on page 2 in order to be compatible with industry convention. (No function specifications and applications have been changed and all the characteristics are kept all the same as Rev 1.3)	Oct. 30. 2013



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FEATURES

■ Fast access time: 10/12ns

low power consumption:

Operating current: 90/80mA (typical) Standby current: 4mA(Typical)

■ Single 3.3V power supply

■ All inputs and outputs TTL compatible

■ Fully static operation

■ Tri-state output

■ Data byte control : LB# (DQ0 ~ DQ7)

UB# (DQ8 ~ DQ15)

■ Data retention voltage : 1.5V (MIN.)

■ Green package available

■ Package : 48-pin 12mm x 20mm TSOP-I

48-ball 6mmx8mm TFBGA

GENERAL DESCRIPTION

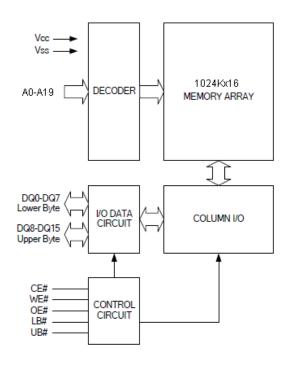
The LY61L102416A is a 16M-bit high speed CMOS static random access memory organized as 1024K words by 16 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The LY61L102416A operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product	Operating	Van Danga	Chood	Power Dissipation		
Family	Temperature	Vcc Range	Speed	Standby(IsB1,TYP.)	Operating(Icc1,TYP.)	
LY61L102416A	0 ~ 70℃	2.7 ~ 3.6V	10/12ns	4mA	90/80mA	
LY61L102416A(I)	-40 ~ 85°C	2.7 ~ 3.6V	10/12ns	4mA	90/80mA	

FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A19	Address Inputs
DQ0 – DQ15	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
LB#	Lower Byte Control
UB#	Upper Byte Control
Vcc	Power Supply
Vss	Ground

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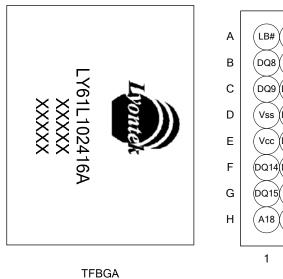
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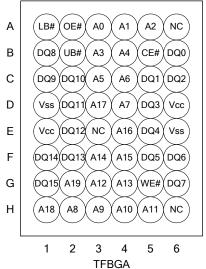
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PIN CONFIGURATION



TSOP-I







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ABSOLUTE MAXIMUN RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V _{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to Vss	VT2	-0.5 to Vcc+0.5	V
Operating Temperature	TA	0 to 70(C grade)	°C
Operating Temperature	IA	-40 to 85(I grade)	C
Storage Temperature	Тѕтс	-65 to 150	$^{\circ}\mathbb{C}$
Power Dissipation	Po	1	W
DC Output Current	Іоит	50	mA

^{*}Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	LB#	UB#	I/O OPE	RATION	SUPPLY CURRENT
WODL	OL#	OL#	***	LD#	DQ0-DQ7 DQ8-DQ		DQ8-DQ15	OOI I EI OOKKENI
Standby	Н	Х	Х	Х	Х	High – Z	High – Z	Isb , I _{SB1} ,
Output Disable	L	Н	Н	Х	Х	High – Z	High – Z	Icc
Output Disable	L	Х	Х	Н	Н	High – Z	High – Z	ICC
	L	L	Н	L	Н	D _{OUT}	High – Z	
Read	L	L	Н	Н	L	High – Z	D_OUT	Icc
	L	L	Н	L	L	D_OUT	D_OUT	
	L	X	L	L	Н	D _{IN}	High – Z	
Write	L	Х	L	Н	L	High – Z	D _{IN}	Icc
	L	Х	L	L	L	D_IN	D _{IN}	

Note: $H = V_{IH}$, $L = V_{IL}$, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP. ^{^4}	MAX.	UNIT
Supply Voltage	Vcc			2.7	3.3	3.6	V
Input High Voltage	V _{IH} ¹			2.2	-	Vcc+0.3	V
Input Low Voltage	V _{IL} ²			- 0.3	-	0.8	V
Input Leakage Current	ILI	$V_{CC} \ge V_{IN} \ge V_{SS}$		- 1	-	1	μA
Output Leakage Current		$V_{CC} \ge V_{OUT} \ge V_{SS}$, Output Disabled		- 1	-	1	μΑ
Output High Voltage	Vон	Iон = -4mA	2.4	-	-	V	
Output Low Voltage	Vol	IoL =8mA		-	-	0.4	V
	lcc	$CE\# = V_{IL}$, $I_{I/O} = 0mA$	-10	-	110	160	mA
AverageOperating	100	;f=max	-12	-	100	140	mA
Power supply		CE# ≦0.2, Other	-10		90	120	mA
Current	lcc1	pin is at 0.2V or Vcc-0.2V II/O = 0mA;f=max	-12		80	110	mA
Standby Power Supply Current	Ich	CE# ≧Vih Other pin is at Vil or Vih		-	-	80	mA



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Standby Power	lona	$CE# \ge V_{CC} - 0.2V$;		4	40	mΛ
Supply Current	ISB1	Other pin is at 0.2V or Vcc-0.2V	-	4	40	mA

Notes:

- 1. $V_{IH}(max) = V_{CC} + 2.0V$ for pulse width less than 6ns.
- 2. VIL(min) = Vss 2.0V for pulse width less than 6ns.
- Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
 Typical values are included for reference only and are not guaranteed or tested.
- Typical valued are measured at $V_{CC} = V_{CC}(TYP.)$ and $T_A = 25^{\circ}C$

CAPACITANCE (TA = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	Cin	-	8	pF
Input/Output Capacitance	C _{I/O}	-	10	pF

Note: These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

speed	10/12ns
Input Pulse Levels	0.2V to Vcc-0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	Vcc/2
Output Load	$C_L = 30pF + 1TTL$,
Output Load	IOH/IOL = -8mA/4mA

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

DADAMETED	SYM.	LY61L102416A-10		LY61L102416A-12		LIMIT
PARAMETER	STIVI.	MIN.	MAX.	MIN.	MAX.	UNIT
Read Cycle Time	t _{RC}	10	-	12	-	ns
Address Access Time	taa	-	10	-	12	ns
Chip Enable Access Time	tace	-	10	-	12	ns
Output Enable Access Time	toe	-	4.5	-	5	ns
Chip Enable to Output in Low-Z	tcLz*	2	-	3	-	ns
Output Enable to Output in Low-Z	tolz*	0	-	0	-	ns
Chip Disable to Output in High-Z	tcHz*	-	4	-	5	ns
Output Disable to Output in High-Z	toнz*	-	4	-	5	ns
Output Hold from Address Change	tон	2	-	2	-	ns
LB#, UB# Access Time	t _{BA}	-	4.5	-	5	ns
LB#, UB# to High-Z Output	tвнz*	-	4	-	5	ns
LB#, UB# to Low-Z Output	t _{BLZ} *	0	-	0	-	ns

(2) WRITE CYCLE

PARAMETER	SYM.	LY61L102416A-10		LY61L102416A-12		LINUT
PARAMETER	STIVI.	MIN.	MAX.	MIN.	MAX.	UNIT
Write Cycle Time	twc	10	-	12	-	ns
Address Valid to End of Write	taw	8	-	10	-	ns
Chip Enable to End of Write	tcw	8	-	10	-	ns
Address Set-up Time	tas	0	-	0	-	ns
Write Pulse Width	twp	8	-	10	-	ns

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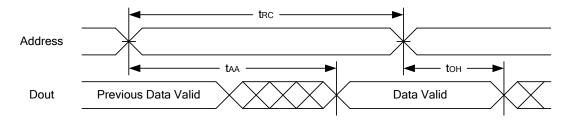
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Write Recovery Time	twr	0	-	0	-	ns
Data to Write Time Overlap	t _{DW}	6	-	7	-	ns
Data Hold from End of Write Time	tон	0	-	0	-	ns
Output Active from End of Write	tow*	2	-	2	-	ns
Write to Output in High-Z	twnz*	-	4	-	5	ns
LB#, UB# Valid to End of Write	t _{BW}	8	-	10	-	ns

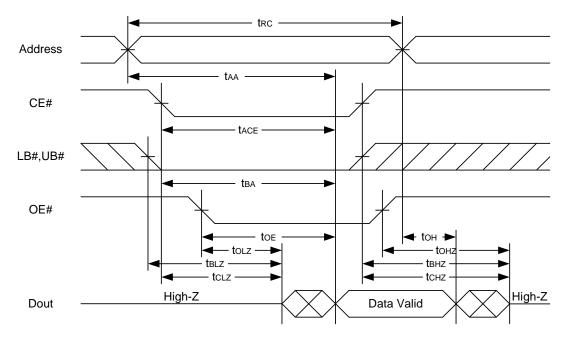
^{*}These parameters are guaranteed by device characterization, but not production tested.

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



Notes:

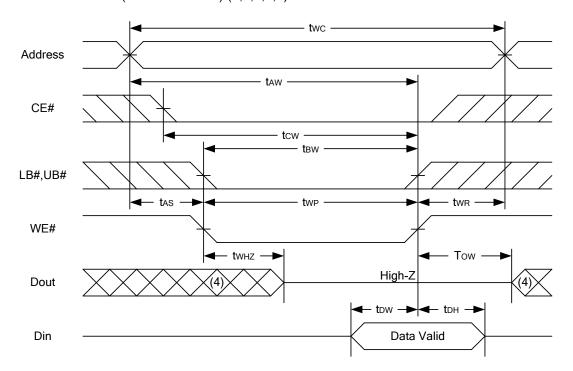
- 1.WE#is high for read cycle.
- 2.Device is continuously selected OE# = low, CE# = low, LB# or UB# = low.
- 3.Address must be valid prior to or coincident with CE# = low, LB# or UB# = low transition; otherwise tAA is the limiting parameter.
- 4.tclz, tblz, tclz, tchz, tbhz and tohz are specified with $C_L = 5pF$. Transition is measured ± 500 mV from steady state.
- $5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} \ , t_{BHZ} is less than t_{BLZ}, t_{OHZ} is less than t_{OLZ}.$



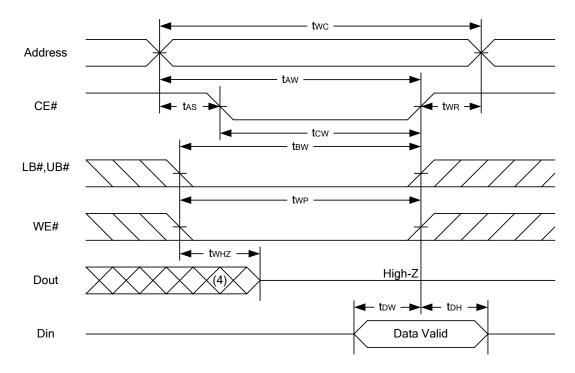
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WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)

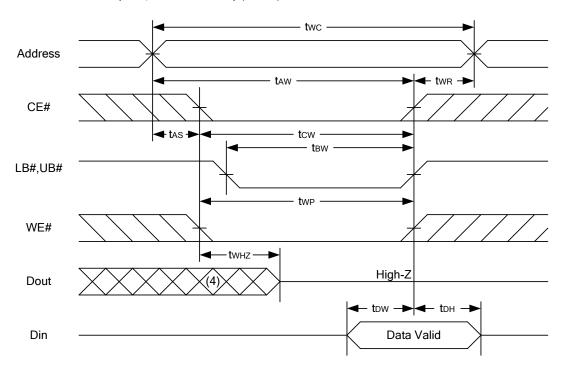




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WRITE CYCLE 3 (LB#,UB# Controlled) (1,2,5,6)



Notes:

- 1.WE#,CE#, LB#, UB# must be high during all address transitions.
- 2.A write occurs during the overlap of a low CE#, low WE#, LB# or UB# = low.
- 3.During a WE# controlled write cycle with OE# low, twp must be greater than twHz + tow to allow the drivers to turn off and data to be placed on the bus.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
- 5.If the CE#, LB#, UB# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- 6.tow and twHz are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.



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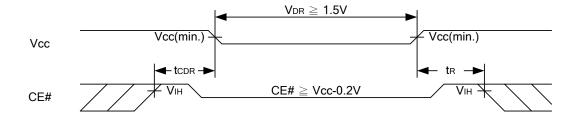
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DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$CE\# \ge V_{CC} - 0.2V$	1.5	-	3.6	V
Data Retention Current		Vcc = 1.5V $CE\# \ge Vcc - 0.2V$; Other pin is at 0.2V or Vcc-0.2V	-	4	40	mA
Chip Disable to Data Retention Time	tcdr	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC∗}	-	-	ns

tRC* = Read Cycle Time

DATA RETENTION WAVEFORM



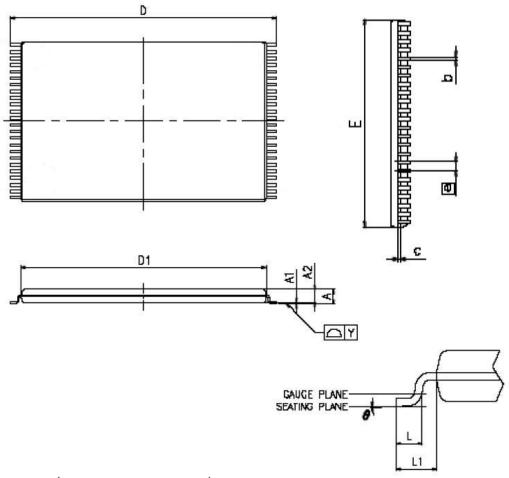


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PACKAGE OUTLINE DIMENSION

48-pin 12mm x 20mm TSOP-I Package Outline Dimension



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

	NIBATION PER BINETIDION TO THE INT.					
	SYMBOLS	MIN.	NOM.	MAX		
	A	1	_	1.20		
	A1	0.05	-	0.15		
	A2	0.95	1.00	1.05		
	р	0.17	0.22	0.27		
	С	0.10	_	0.21		
Δ	0	19.80	20.00	20.20		
Δ	□1	18.30	18.40	18.50		
Δ	E	11.90	12.00	12.10		
	₽	0.50 BASIC				
	L	0.50	0.60	0.70		
Λ	L1	ı	ე.80	_		
Δ	Υ	_	_	0.10		
Δ	θ	D.	_	5*		

NOTES:

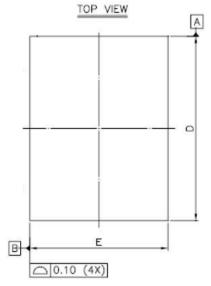
- 1 JEDEC OUTLINE : MO-142 DO
- 2.PROFILE TOLERANCE ZONES FOR D1 AND E DD NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION ON E IS 0.15 mm PER SIDE AND ON D1 IS 0.25 mm PER SIDE.
- 3.DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08mm TOTAL IN EXCESS OF THE & DIMENSION AT NAXIMUN MATERIAL CONDITION DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT.

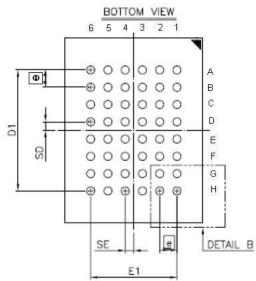


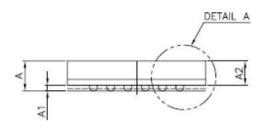
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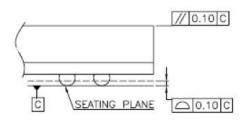
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48-ball 6mm × 8mm TFBGA Package Outline Dimension





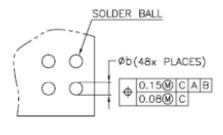




SIDE VIEW

DETAIL A

CVAL	DIMENSION (mm)			DIMENSION (inch)			
SYM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α		_	1.40	_	_	0.055	
A1	0.20	0.25	0.30	0.008	0.010	0.012	
A2	_	_	1.05	_	_	0.041	
Ь	0.30	0.35	0.40	0.012	0.014	0.016	
D	7.95	8.00	8.05	0.313	0.315	0.317	
D1	5.25 BSC			0.207 BSC			
Ε	5.95	6.00	6.05	0.234	0.236	0.238	
E1	3.75 BSC			0.148 BSC			
SE	0.375 TYP			0.015 TYP			
SD	0	.375 TY	P	0.015 TYP			
e	0.75 BSC			0.030 BSC			



DETAIL B

NOTE:

- CONTROLLING DIMENSION: MILLIMETER.
- REFERENCE DOCUMENT : JEDEC MO-207.

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ORDERING INFORMATION

Package Type	Access Time (Speed)(ns)	Temperature Range(℃)	Packing Type	Lyontek Item No.
48-pin(12mmx20mm)	10	0℃~70℃	Tray	LY61L102416ALL-10
TSOP-I			Tape Reel	LY61L102416ALL-10T
		-40°C~85°C	Tray	LY61L102416ALL-10I
			Tape Reel	LY61L102416ALL-10IT
	12	0℃~70℃	Tray	LY61L102416ALL-12
			Tape Reel	LY61L102416ALL-12T
		-40°C~85°C	Tray	LY61L102416ALL-12I
			Tape Reel	LY61L102416ALL-12IT
48-Ball 6mmx8mm TFBGA	10	0℃~70℃	Tray	LY61L102416AGL-10
			Tape Reel	LY61L102416AGL-10T
		-40°C~85°C	Tray	LY61L102416AGL-10I
			Tape Reel	LY61L102416AGL-10IT
	12 0℃	0°C~70°C	Tray	LY61L102416AGL-12
			Tape Reel	LY61L102416AGL-12T
		-40℃~85℃	Tray	LY61L102416AGL-12I
			Tape Reel	LY61L102416AGL-12IT



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